

Supporting Information:

The Enhanced Ferromagnetism of Single-Layer CrX₃ (X=Br and I) by
Van der Waals Engineering

Hongxing Li,^{a,b} Yuan-Kai Xu,^{a,b} Kang Lai,^{a,b} and Wei-Bing Zhang,^{a,b*}

*a School of Physics and Electronic Sciences, Changsha University of Science and
Technology, Changsha 410114, People's Republic of China.*

*b Hunan Provincial Key Laboratory of Flexible Electronic Materials Genome
Engineering, Changsha University of Science and Technology, Changsha 410114,
People's Republic of China*

E-mail: zhangwb@csust.edu.cn

Phone: +86(0)73185258223. Fax: +86(0)73185258217

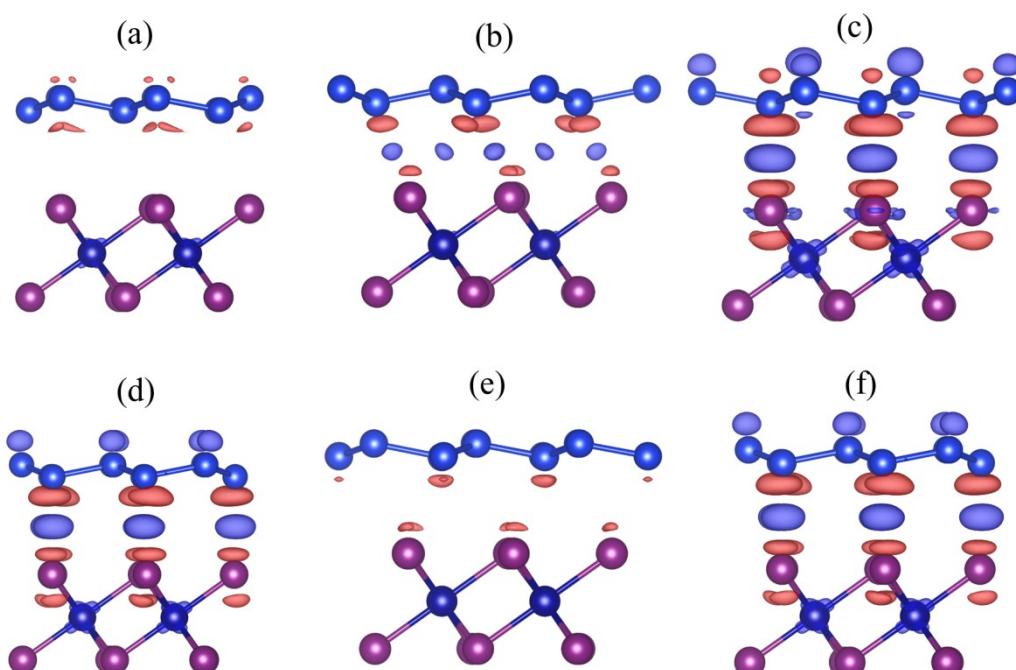


Fig. S1 Charge difference density of Si/CrI₃ for difference configuration (a)(d)
TX_up/dn, (b)(e) TbX_up/dn, (c)(f) TuX_up/dn. The blue and red represent the
charge accumulation and depletion, the isosurface is set as 0.0005 eV·Å³

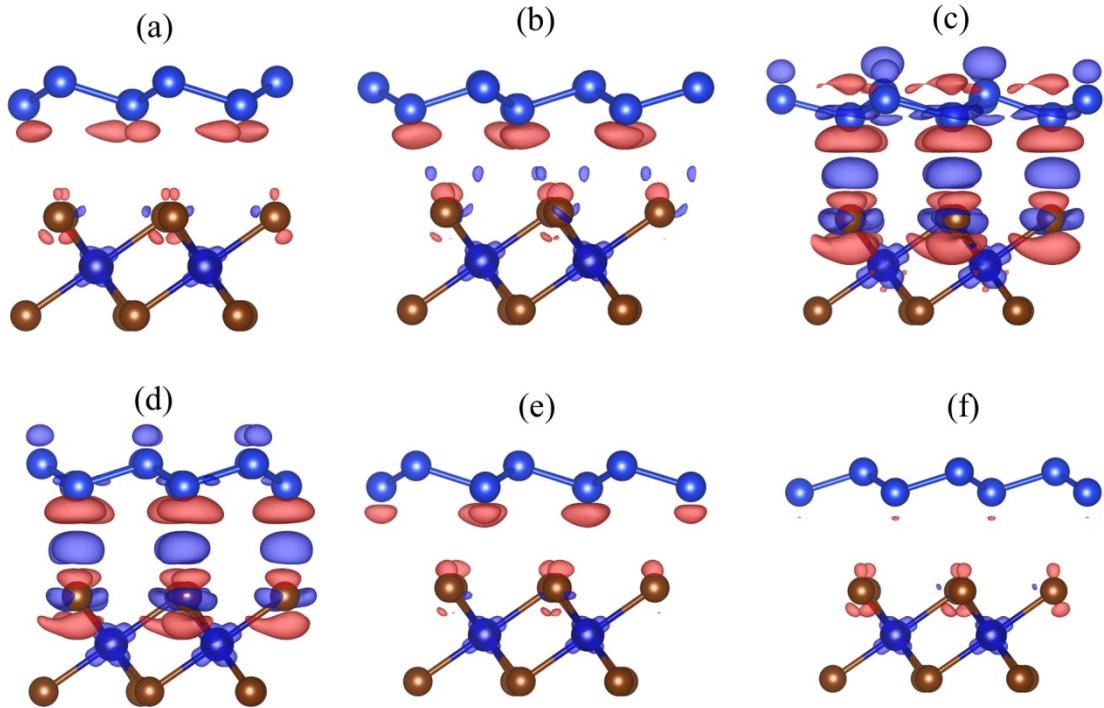


Fig. S2 Charge difference density of Si/CrBr₃ for difference configuration (a)(d) TX_up/dn, (b)(e) TbX_up/dn, (c)(f) TuX_up/dn. The blue and red represent the charge accumulation and depletion, the isosurface is set as 0.0005 eV·Å³

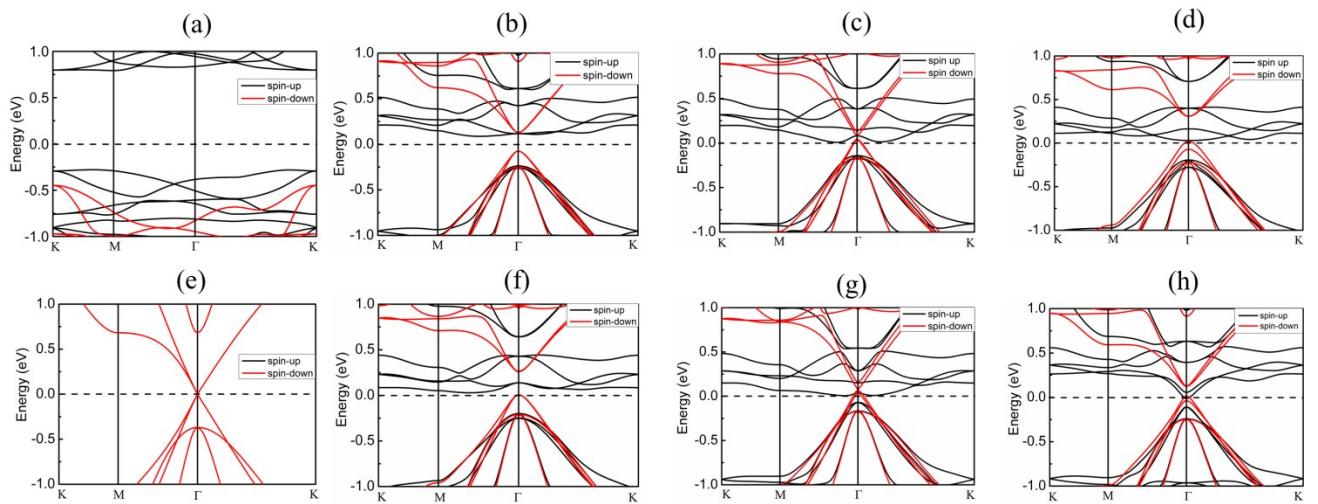


Fig. S3 The spin-polarized band structure of Ge/CrI₃ at different configurations. (b)(f) TX_up/dn, (c)(g) TbX_up/dn, (d)(h) TuX_up/dn. (a)(e) the band of single-layer CrI₃ and germanene

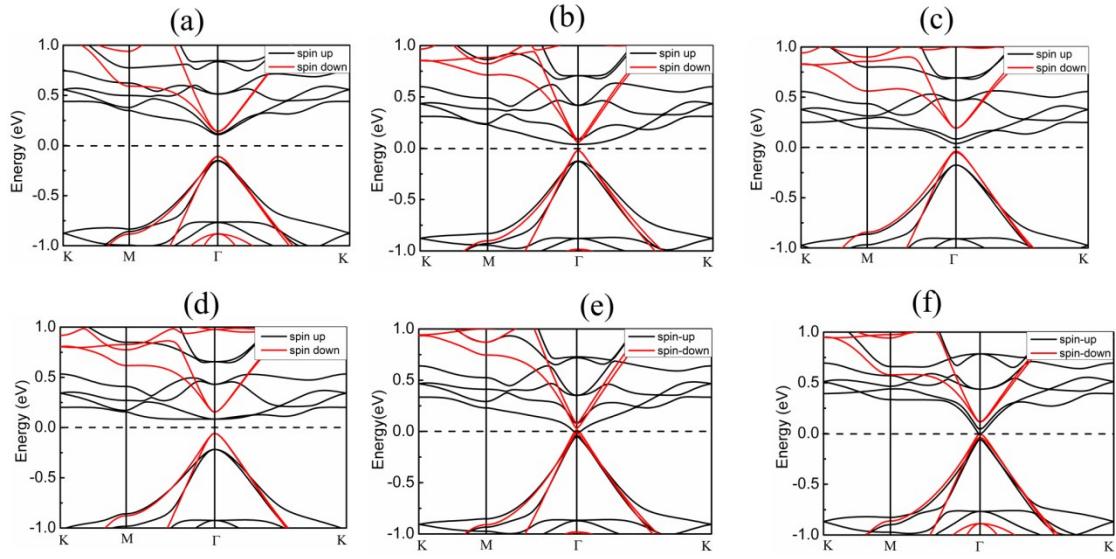


Fig. S4 The spin-polarized band structure of Si/CrI₃ at different configurations. (a)(d) TX_up/dn, (b)(e) TbX_up/dn, (c)(f) TuX_up/dn

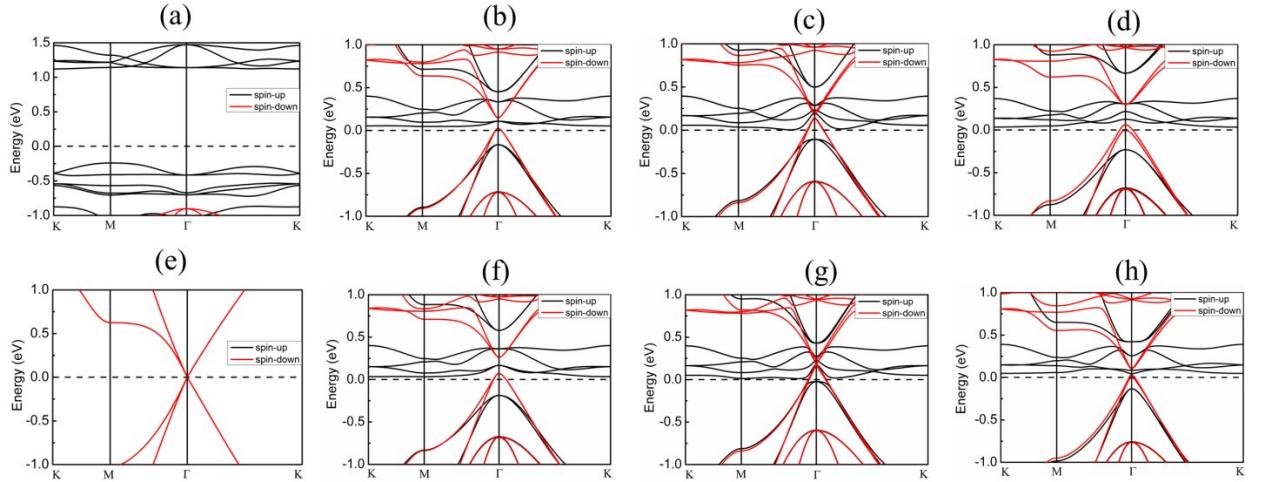


Fig. S5 The spin-polarized band structure of Si/CrBr₃ at different configurations. (b)(f) TX_up/dn, (c)(g) TbX_up/dn, (d)(h) TuX_up/dn. (a)(e) the band of single-layer CrBr₃ and silicene.